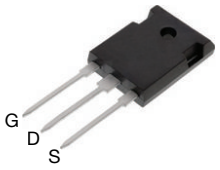
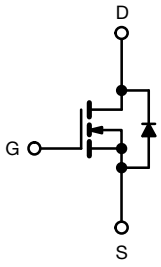
EF Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY		
V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ typ. at 25 °C (Ω)	V_{GS} = 10 V	0.033
Q_g (Max.) (nC)	380	
Q_{gs} (nC)	62	
Q_{gd} (nC)	102	
Configuration	Single	

TO-247AD





N-Channel MOSFET

FEATURES

- Fast body diode MOSFET using E series technology
- Reduced t_{rr}, Q_{rr}, and I_{RRM}
- Low figure-of-merit (FOM): R_{on} x Q_g
- Low input capacitance (C_{iss})
- Increased robustness due to low Q_{rr}
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Lighting
  - High intensity discharge (HID)
  - Light emitting diodes (LEDs)
- Consumer and computing
  - ATX power supplies
- Industrial
  - Welding
  - Battery chargers
- Renewable energy
  - Solar (PV inverters)
- Switch mode power suppliers (SMPS)
- Applications using the following topologies
  - LLC
  - Phase shifted bridge (ZVS)
  - 3-level inverter
  - AC/DC bridge

ORDERING INFORMATION	
Package	TO-247AD
Lead (Pb)-free and Halogen-free	SiHW70N60EF-GE3

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	600	V
Gate-Source Voltage			V_{GS}	± 30	
Continuous Drain Current (T_J = 150 °C)	V_{GS} at 10 V	T_C = 25 °C	I_D	70	A
		T_C = 100 °C		45	
Pulsed Drain Current [a]			I_{DM}	229	
Linear Derating Factor				4.2	W/°C
Single Pulse Avalanche Energy [b]			E_{AS}	1706	mJ
Maximum Power Dissipation			P_D	520	W
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	T_J = 125 °C		dV/dt	70	V/ns
Reverse Diode dV/dt [d]				50	
Soldering Recommendations (Peak Temperature) [c]	for 10 s			300	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 11 A
c. 1.6 mm from case
d. I_{SD} = 35 A, dI/dt = 750 A/µs, V_{DS} = 400 V

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.24	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.69	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
		V_{GS} = ± 30 V	-	-	± 1	µA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 480 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 480 V, V_{GS} = 0 V, T_J = 125 °C	-	-	2	mA
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 35 A	-	0.033	0.038	Ω
Forward Transconductance	g_{fs}	V_{DS} = 30 V, I_D = 35 A	-	25	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 100 V, f = 1 MHz	-	7500	-	pF
Output Capacitance	C_{oss}		-	378	-	
Reverse Transfer Capacitance	C_{rss}		-	5	-	
Effective output capacitance, energy related [a]	$C_{o(er)}$	V_{GS} = 0 V, V_{DS} = 0 V to 480 V	-	263	-	
Effective output capacitance, time related [b]	$C_{o(tr)}$		-	926	-	
Total Gate Charge	Q_g	V_{GS} = 10 V; I_D = 35 A, V_{DS} = 480 V	-	253	380	nC
Gate-Source Charge	Q_{gs}		-	62	-	
Gate-Drain Charge	Q_{gd}		-	102	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 480 V, I_D = 35 A, R_g = 9.1 Ω, V_{GS} = 10 V	-	56	84	ns
Rise Time	t_r		-	107	161	
Turn-Off Delay Time	$t_{d(off)}$		-	257	386	
Fall Time	t_f		-	123	185	
Gate Input Resistance	R_g	f = 1 MHz, open drain	0.5	1.1	2.2	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	70	A
Pulsed Diode Forward Current	I_{SM}		-	-	229	
Diode Forward Voltage	V_{SD}	T_J = 25 °C, I_S = 35 A, V_{GS} = 0 V	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = I_S = 35 A, dI/dt = 100 A/µs, V_R = 400 V	-	213	426	ns
Reverse Recovery Charge	Q_{rr}		-	1.6	3.2	µC
Reverse Recovery Current	I_{RRM}		-	16	-	A

Notes

a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

b. $C_{oss(tr)}$ is a fixed capacitance that gives the charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

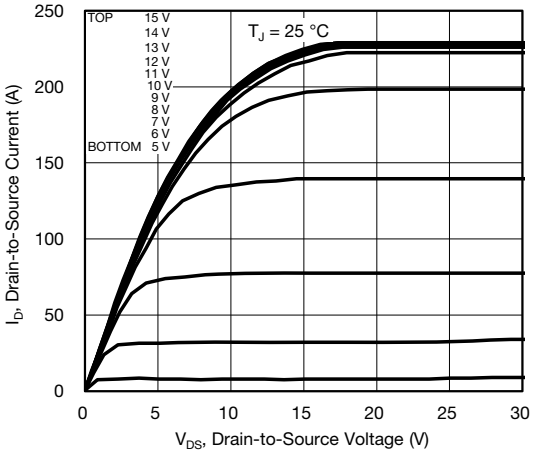


Fig. 1 - Typical Output Characteristics

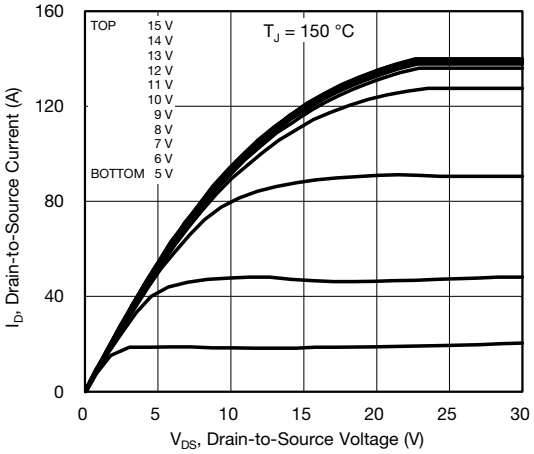


Fig. 2 - Typical Output Characteristics

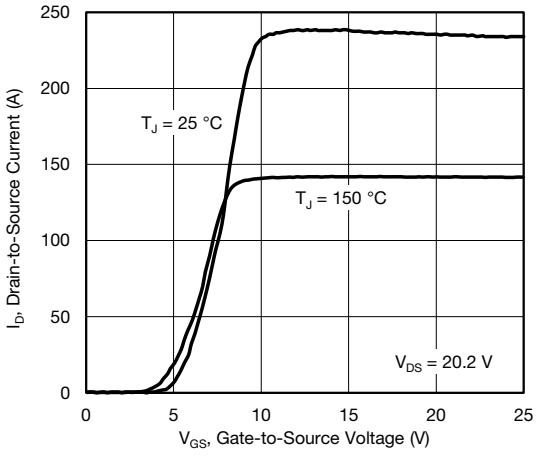


Fig. 3 - Typical Transfer Characteristics

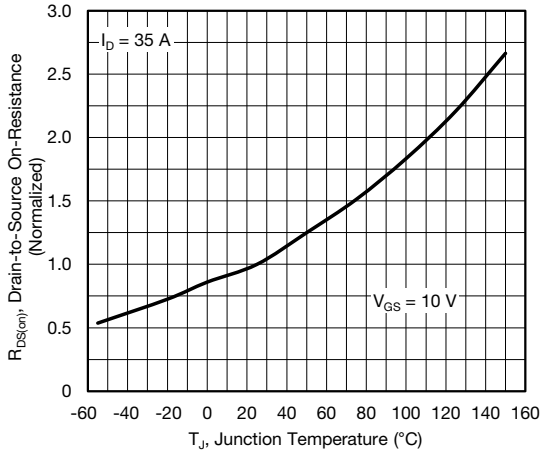


Fig. 4 - Normalized On-Resistance vs. Temperature

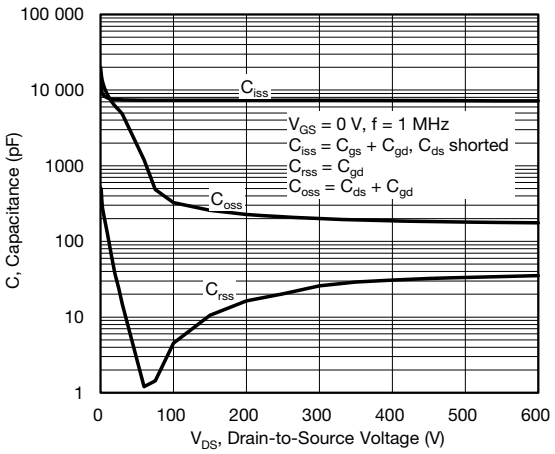


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

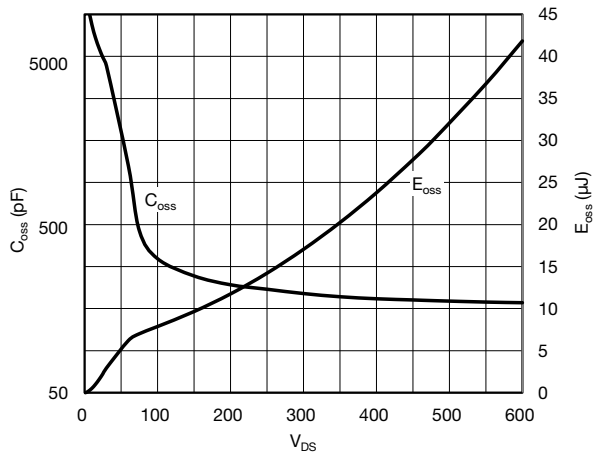


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

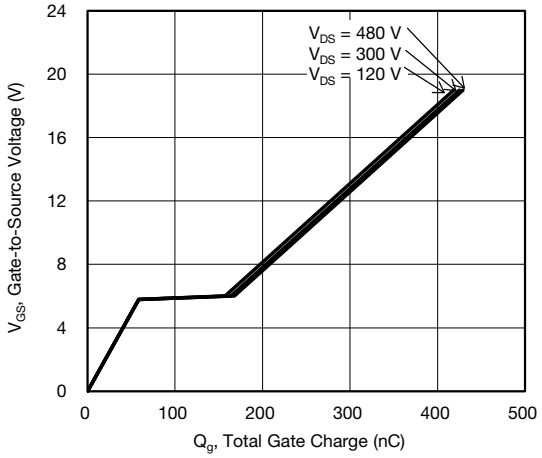


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

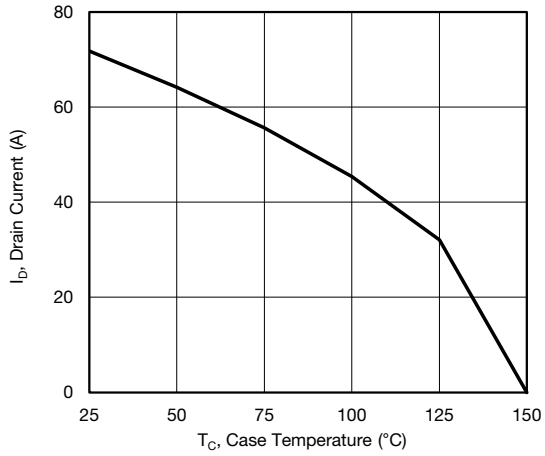


Fig. 10 - Maximum Drain Current vs. Case Temperature

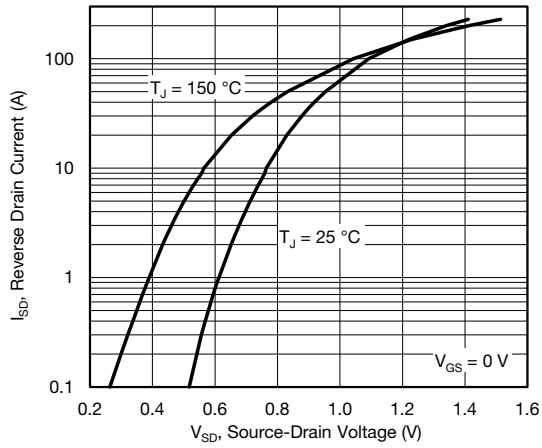


Fig. 8 - Typical Source-Drain Diode Forward Voltage

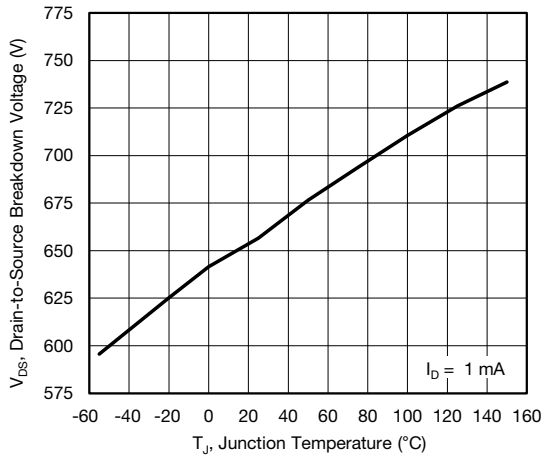


Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

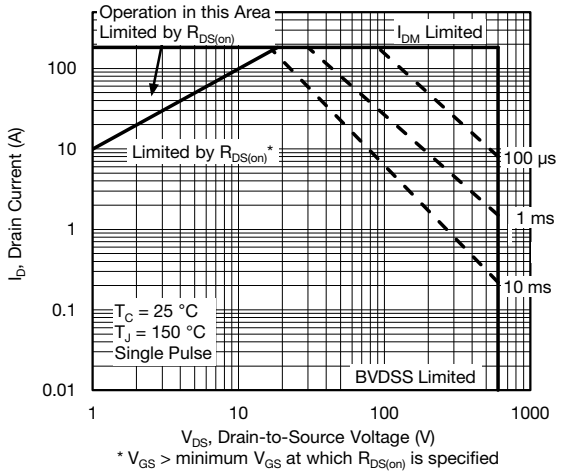


Fig. 9 - Maximum Safe Operating Area

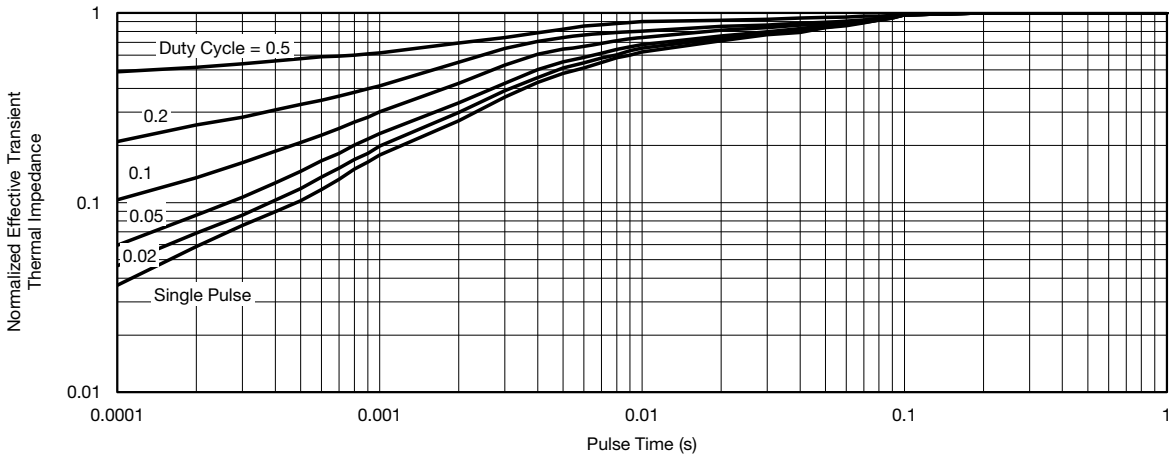


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

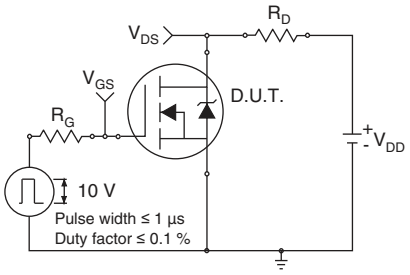


Fig. 13 - Switching Time Test Circuit

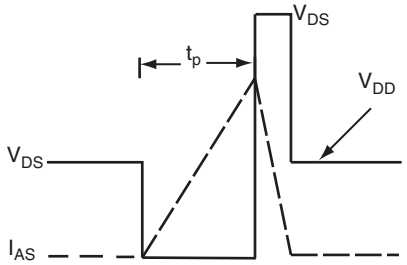


Fig. 16 - Unclamped Inductive Waveforms

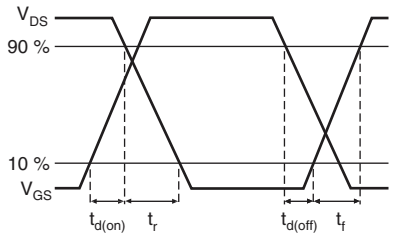


Fig. 14 - Switching Time Waveforms

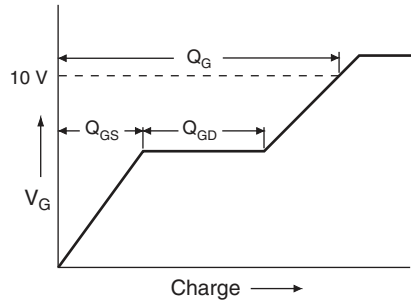


Fig. 17 - Basic Gate Charge Waveform

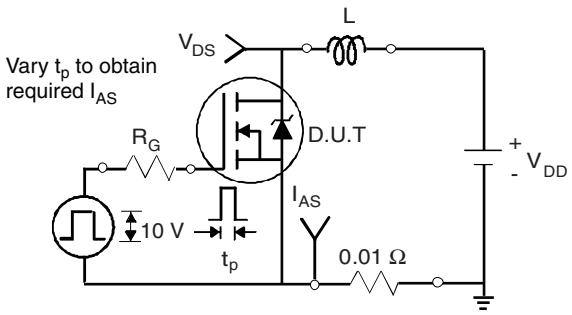


Fig. 15 - Unclamped Inductive Test Circuit

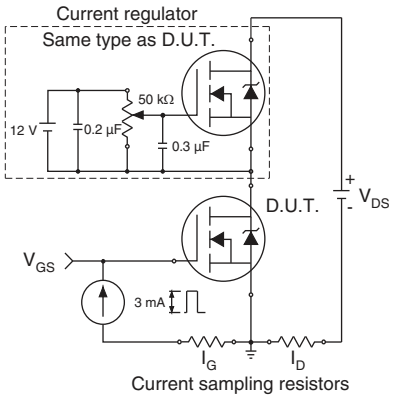
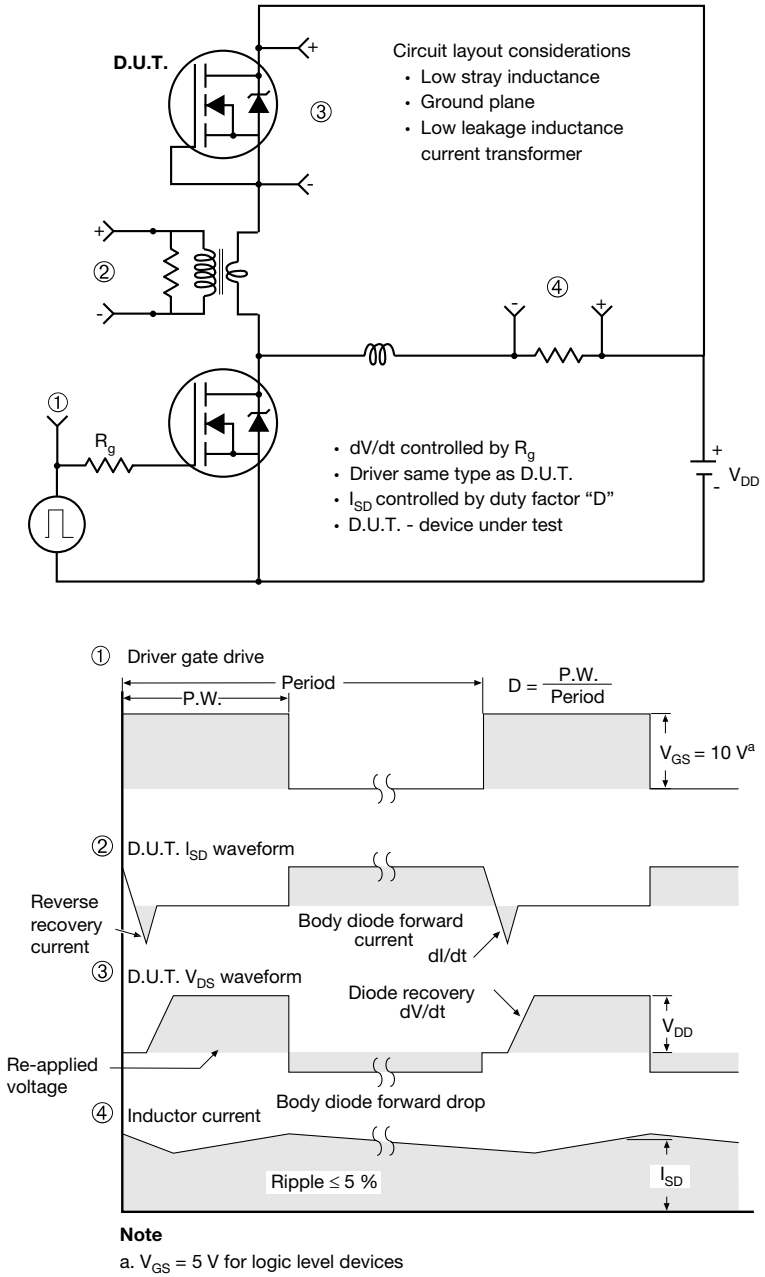


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

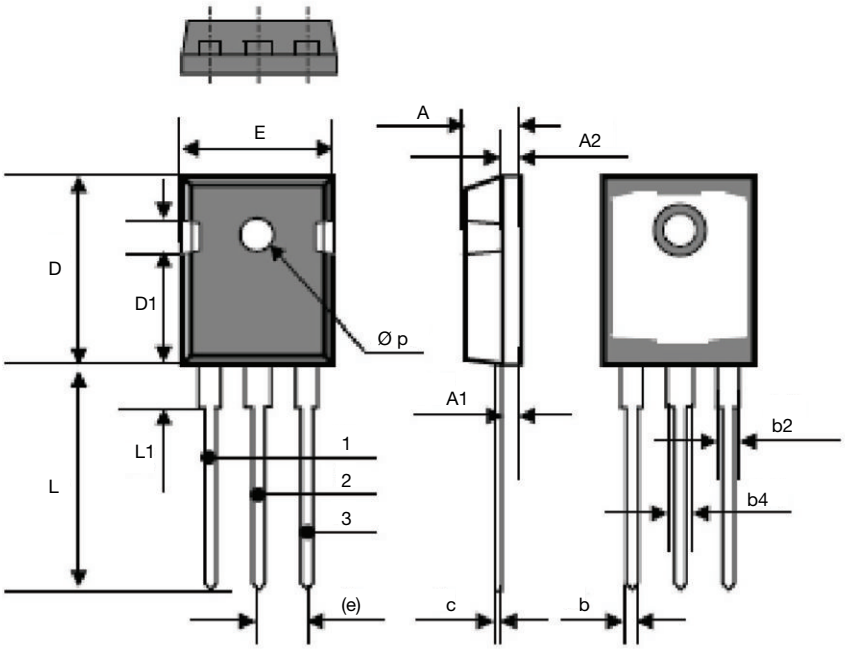


Note

a. V_{GS} = 5 V for logic level devices

Fig. 19 - For N-Channel

TO-247AD (High Voltage)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.41	0.065	0.095
b4	2.59	3.43	0.102	0.135
c	0.61 BSC		0.024 BSC	
D	20.80	21.46	0.819	0.845
D1	3.68	5.49	0.145	0.216
(e)	5.46 BSC		0.215 BSC	
E	15.49	16.26	0.610	0.640
L	19.81	20.32	0.780	0.800
L1	4.06	4.50	0.160	0.177
Ø p	3.51	3.66	0.138	0.144
ECN: S17-0178-Rev. B, 06-Feb-17 DWG: 6010				

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